

2SA715

Silicon PNP Epitaxial

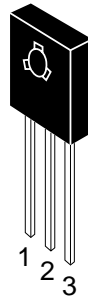
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Application

Low frequency power amplifier complementary pair with 2SC1162

Outline

TO-126 MOD



1. Emitter
2. Collector
3. Base

Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Rating	Unit
Collector to base voltage	V_{CBO}	-35	V
Collector to emitter voltage	V_{CEO}	-35	V
Emitter to base voltage	V_{EBO}	-5	V
Collector current	I_C	-2.5	A
Collector peak current	$I_{C(peak)}$	-3	A
Collector power dissipation	P_C	0.75	W
	P_C^{*1}	10	W
Junction temperature	T_j	150	°C
Storage temperature	T_{stg}	-55 to +150	°C

Note: 1. Value at $T_C = 25^\circ\text{C}$

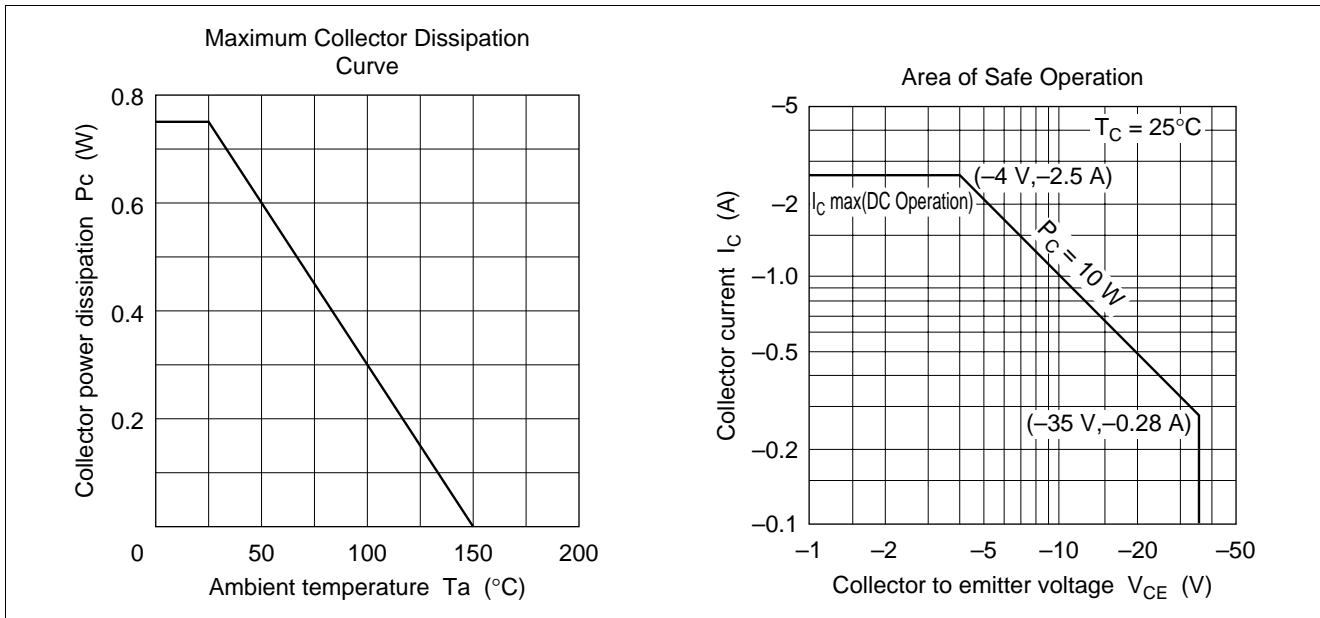
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Electrical Characteristics (T_a = 25°C)

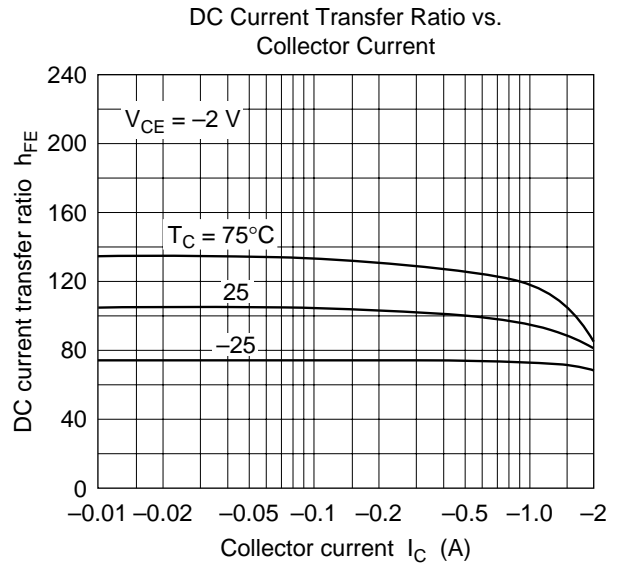
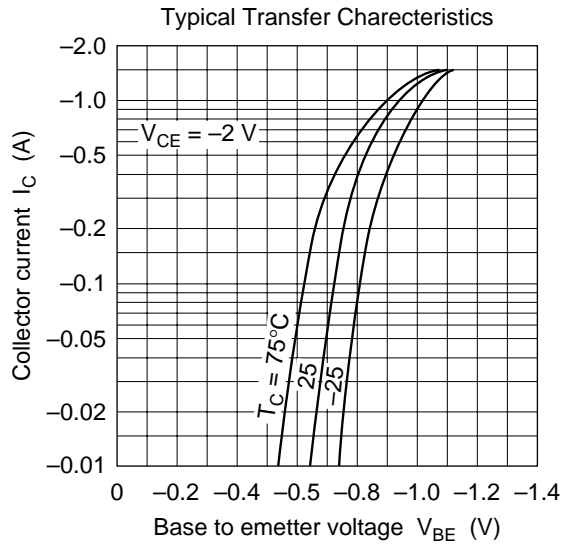
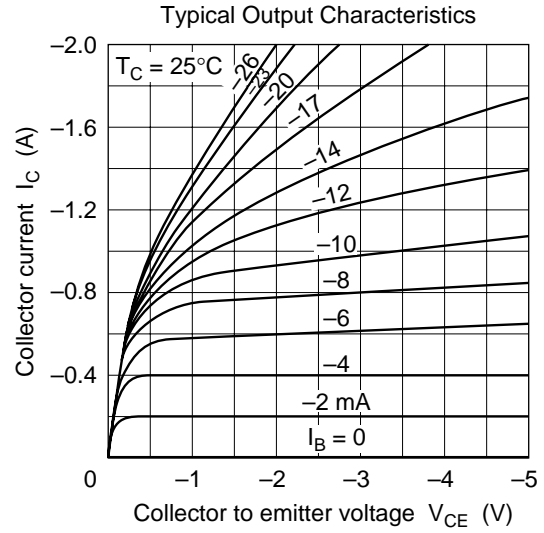
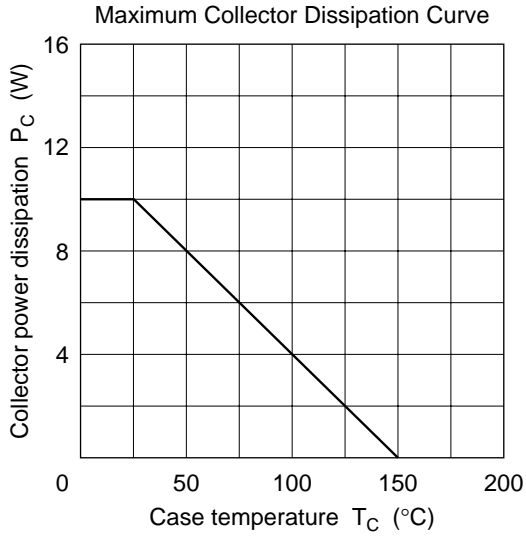
Item	Symbol	Min	Typ	Max	Unit	Test conditions
Collector to base breakdown voltage	V _{(BR)CBO}	-35	—	—	V	I _C = -1 mA, I _E = 0
Collector to emitter breakdown voltage	V _{(BR)CEO}	-35	—	—	V	I _C = -10 mA, R _{BE} = ∞
Emitter to base breakdown voltage	V _{(BR)EBO}	-5	—	—	V	I _E = -1 mA, I _C = 0
Collector cutoff current	I _{CBO}	—	—	-20	μA	V _{CB} = -35 V, I _E = 0
DC current transfer ratio	h _{FE} ^{*1}	60	—	320		V _{CE} = -2 V, I _C = -0.5 A
	h _{FE}	20	—	—		V _{CE} = -2 V, I _C = -1.5 A (Pulse test)
Base to emitter voltage	V _{BE}	—	-1.0	-1.5	V	V _{CE} = -2 V, I _C = -1.5 A (Pulse test)
Collector to emitter saturation voltage	V _{CE(sat)}	—	-0.5	-1.0	V	I _C = -2 A, I _B = -0.2 A (Pulse test)
Gain bandwidth product	f _T	—	160	—	MHz	V _{CE} = -2 V, I _C = -0.2 A (Pulse test)

Note: 1. The 2SA715 is grouped by h_{FE} as follows.

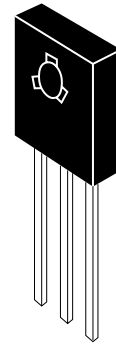
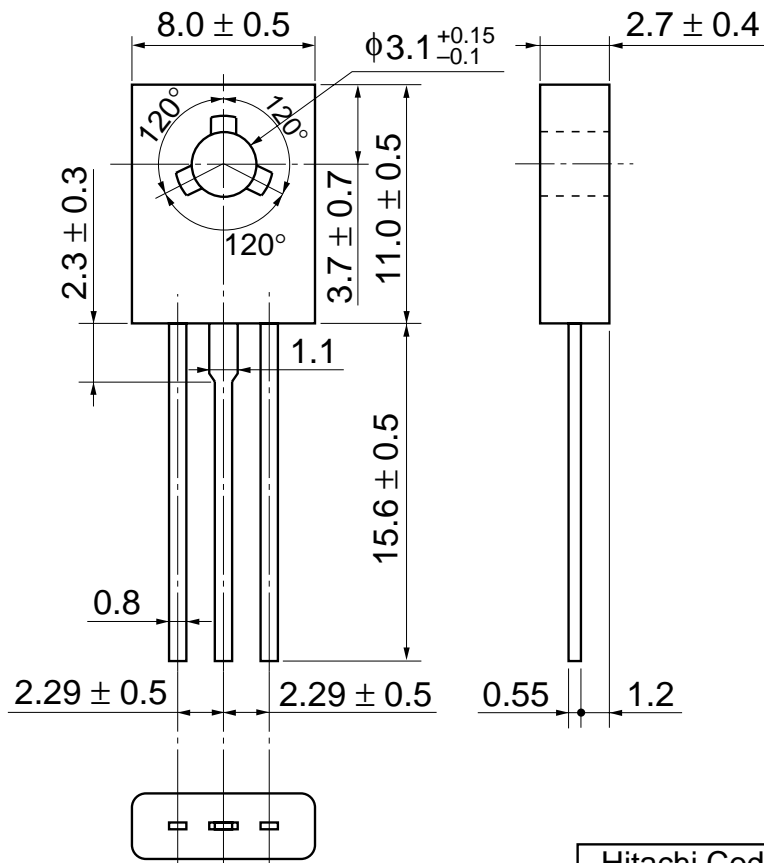
B	C	D
60 to 120	100 to 200	160 to 320



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Unit: mm



Hitachi Code	TO-126 Mod
JEDEC	—
EIAJ	—
Weight (reference value)	0.67 g

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